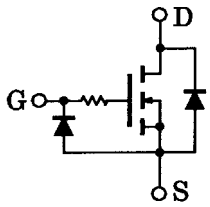
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1825

High Speed Switching Applications
Analog Switch Applications

- 4 V gate drive
- Low threshold voltage: V_{th} = 0.8~2.5 V
- High speed
- Enhancement-mode
- Small package

Equivalent Circuit

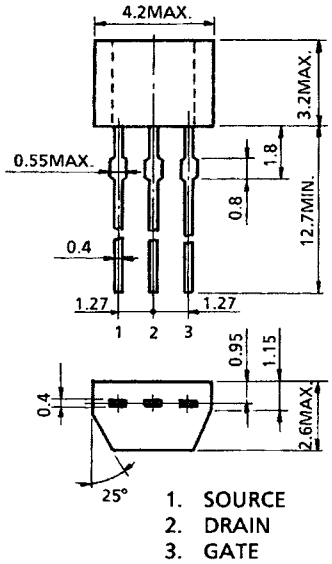


Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	50	V
Gate-source voltage	V_{GSS}	10	V
DC drain current	I_D	50	mA
Drain power dissipation	P_D	300	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Note: This transistor is electrostatic sensitive device.
Please handle with caution.

Unit: mm



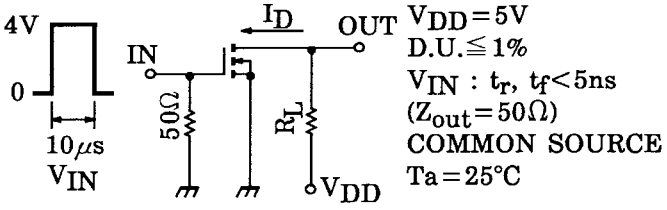
JEDEC	—
JEITA	—
TOSHIBA	2-4E1E

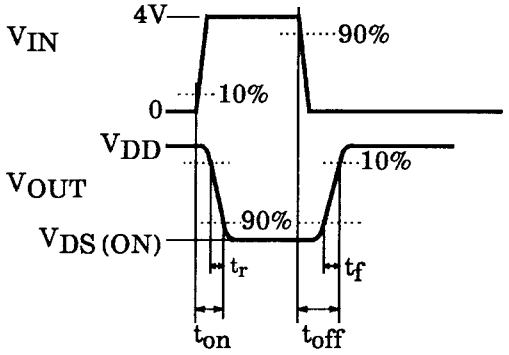
Weight: 0.13 g (typ.)

Electrical Characteristics (Ta = 25°C)

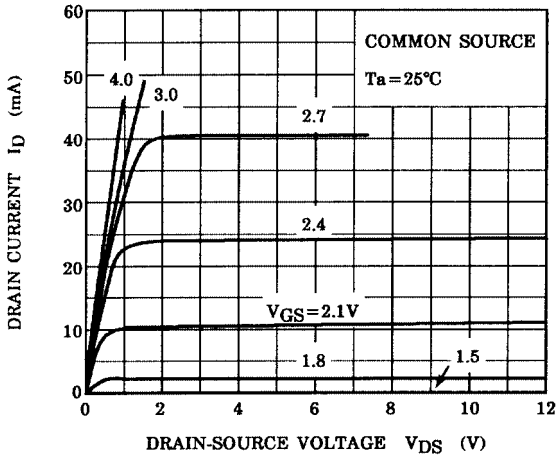
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = 10 V, V_{DS} = 0	—	—	1	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 100 μA, V_{GS} = 0	50	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = 50 V, V_{GS} = 0	—	—	1	μA
Gate threshold voltage		V_{th}	V_{DS} = 5 V, I_D = 0.1 mA	0.8	—	2.5	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 5 V, I_D = 10 mA	20	—	—	mS
Drain-source ON resistance		$R_{DS\ (ON)}$	I_D = 10 mA, V_{GS} = 4.0 V	—	20	50	Ω
Input capacitance		C_{iss}	V_{DS} = 5 V, V_{GS} = 0, f = 1 MHz	—	6.3	—	pF
Reverse transfer capacitance		C_{rss}	V_{DS} = 5 V, V_{GS} = 0, f = 1 MHz	—	1.3	—	pF
Output capacitance		C_{oss}	V_{DS} = 5 V, V_{GS} = 0, f = 1 MHz	—	5.7	—	pF
Switching time	Turn-on time	t_{on}	V_{DD} = 5 V, I_D = 10 mA, V_{GS} = 0~4.0 V	—	0.11	—	μs
	Turn-off time	t_{off}	V_{DD} = 5 V, I_D = 10 mA, V_{GS} = 0~4.0 V	—	0.15	—	

Switching Time Test Circuit

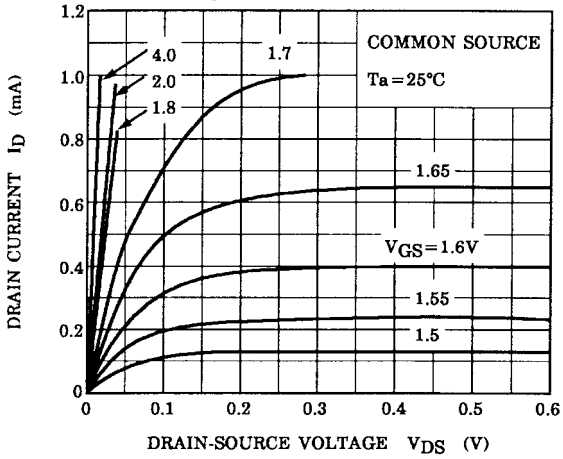




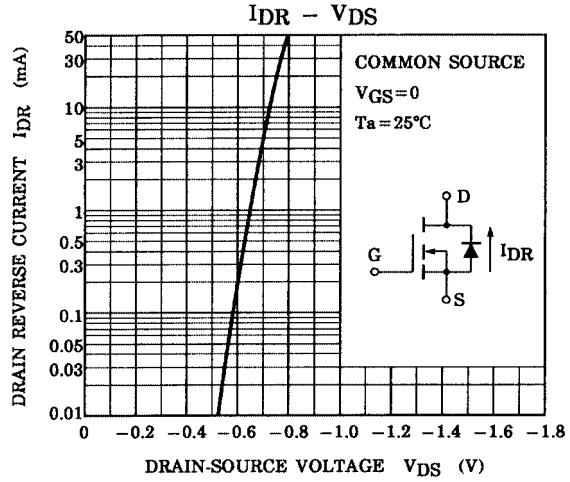
I_D – V_{DS}



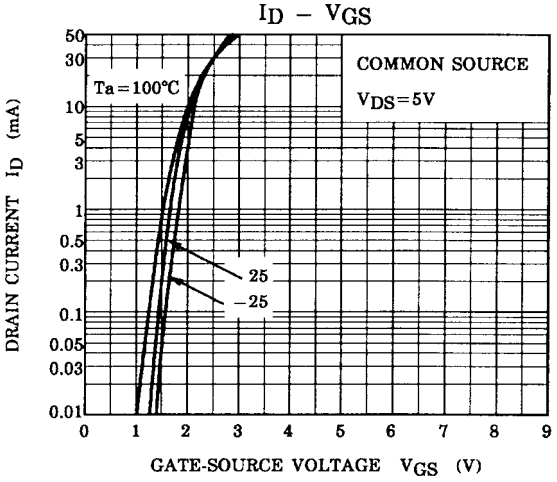
I_D – V_{DS} (LOW VOLTAGE REGION)



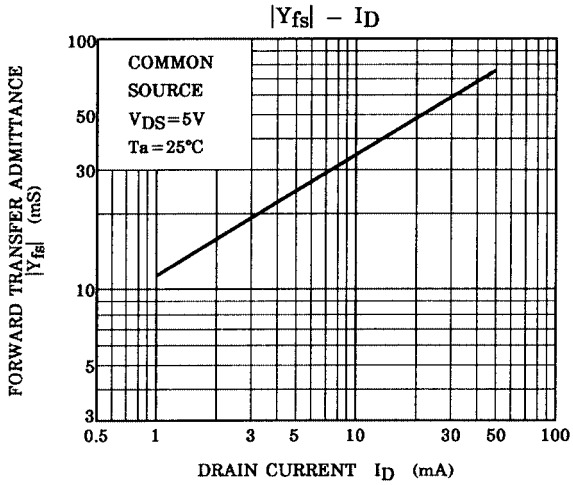
I_{DR} – V_{DS}



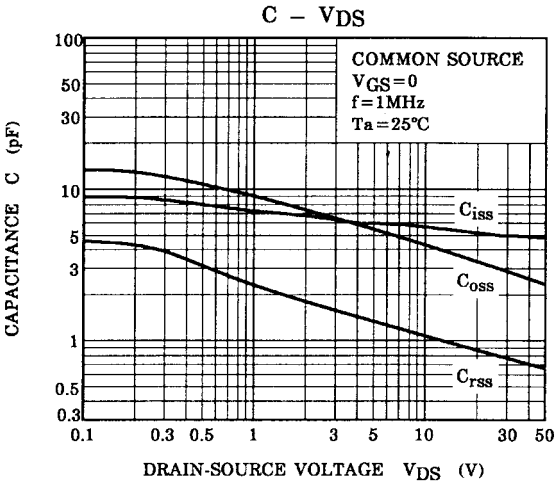
I_D – V_{GS}



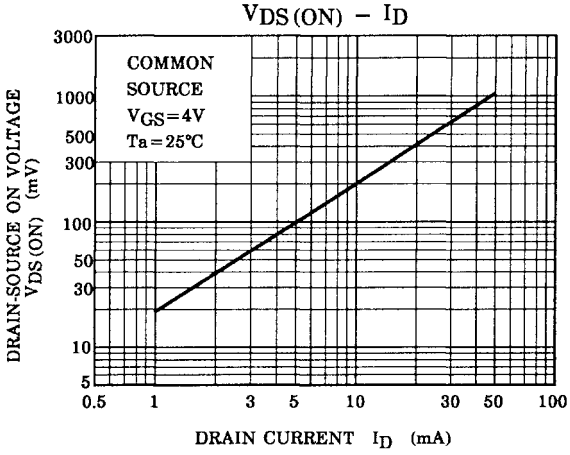
$|Y_{fs}|$ – I_D



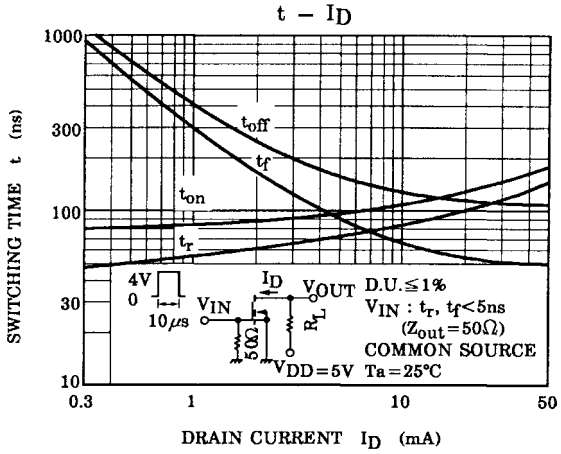
C – V_{DS}



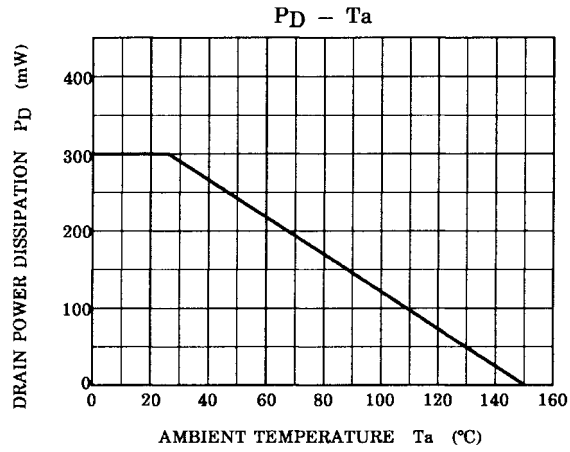
$V_{DS\,(ON)}$ – I_D



t – I_D



P_D – Ta



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